

ABSTRACT

The present invention allows the electrostatically attracting electrode, whose size corresponds to large-diameter wafers, to be fabricated easily and with precision.

5 The first electrode 1 is provided with a recess in which to install the second electrode 2. An insulating film 4 is formed in the recess and then the second electrode is securely fitted in the recess. The assembled electrode is machined to make the surfaces of the first and second electrodes flush
10 with each other in the same plane. The flat surfaces are covered with the sprayed electrostatic attraction film 3, which is then polished until it has a predetermined thickness. This fabrication process allows the electrostatic attraction electrode suitable to large-diameter wafers.

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